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|---|----------------|----------------------|---------------------|------------------|
| APPLICATION NO. | FILING DATE | FIRST NAMED INVENTOR | ATTORNEY DOCKET NO. | CONFIRMATION NO. |
| 09/775,231 | 02/01/2001 | Han-Sin Lee | SAM-167 | 9048 |
| | 590 03/26/2003 | • | | |
| MILLS & ONELLO, LLP ELEVEN BEACON STREET | | | EXAMINER | |
| SUITE 605 BOSTON, MA 02108 | | | POMPEY, RON EVERETT | |
| 2001011, 11111 | | | ART UNIT | PAPER NUMBER |
| | | | 2812 | |

DATE MAILED: 03/26/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

| | | 92 | | | | |
|--|---|--|--|--|--|--|
| _ | Application No. | Applicant(s) | | | | |
| Offic Acti n Summan | 09/775,231 | LEE ET AL. | | | | |
| Offic Acti n Summary | Examiner | Art Unit | | | | |
| The MAILING DATE of this communication and | Ron E Pompey | 2812 | | | | |
| The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply | | | | | | |
| A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply - If NO period for reply is specified above, the maximum statutory period w - Failure to reply within the set or extended period for reply will, by statute, - Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b). Status | i6(a). In no event, however, may a reply be tim within the statutory minimum of thirty (30) days ill apply and will expire SIX (6) MONTHS from to become ARANDONE | s will be considered timely. the mailing date of this communication. | | | | |
| 1) Responsive to communication(s) filed on <u>04 N</u> | <u>farch 2003</u> . | | | | | |
| 2a) This action is FINAL . 2b) ⊠ Thi | s action is non-final. | | | | | |
| 3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213. Disposition of Claims | | | | | | |
| 4)⊠ Claim(s) <u>1,2 and 4-12</u> is/are pending in the app | plication | | | | | |
| 4a) Of the above claim(s) is/are withdraw | | | | | | |
| 5) Claim(s) is/are allowed. | | | | | | |
| 6)⊠ Claim(s) <u>1,2 and 4-12</u> is/are rejected. | | | | | | |
| 7) Claim(s) is/are objected to. | | | | | | |
| 8) Claim(s) are subject to restriction and/or election requirement. | | | | | | |
| Application Papers | | | | | | |
| 9)☐ The specification is objected to by the Examiner. | | | | | | |
| 10)☐ The drawing(s) filed on is/are: a)☐ accepted or b)☐ objected to by the Examiner. | | | | | | |
| Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a). | | | | | | |
| 11) The proposed drawing correction filed on is: a) approved b) disapproved by the Examiner. | | | | | | |
| If approved, corrected drawings are required in reply to this Office action. | | | | | | |
| 12) The oath or declaration is objected to by the Examiner. | | | | | | |
| Priority under 35 U.S.C. §§ 119 and 120 13) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). | | | | | | |
| a) All b) Some * c) None of: | priority under 35 U.S.C. § 119(a)- | -(d) or (f). | | | | |
| · _ ·— ·— | have been received | | | | | |
| 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No. | | | | | | |
| | | | | | | |
| 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. | | | | | | |
| 14) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application). | | | | | | |
| a) The translation of the foreign language provisional application has been received. 15) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121. | | | | | | |
| Attachment(s) | | | | | | |
|) Notice of References Cited (PTO-892)) Notice of Draftsperson's Patent Drawing Review (PTO-948)) Information Disclosure Statement(s) (PTO-1449) Paper No(s) | 5) Notice of Informal Pa | PTO-413) Paper No(s) tent Application (PTO-152) | | | | |
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DETAILED ACTION

Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 1, 2 and 4-12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Laparra et al. (US 6,319,796) and in further view of Park et al. (US 6,326,282) and Shin et al. (US 6,184,077).

Laparra discloses the steps of:

For claims 1, 2 and 4-6:

etching the exposed semiconductor substrate, using the etching mask pattern as an etching mask, to form a trench;

providing a material layer (40b, fig. 4) on the insulating layer (40a, fig. 4) filling the trench;

planarly etching the material layer and the insulating layer down to a top surface of the etching mask pattern to form a device isolation layer pattern in the trench; and removing the exposed etching mask pattern (col. 4, lns. 5-10 and col. 5, lns. 51-56).

Laparra discloses all the steps of claims 1-12 except those described below.
 However Park discloses the steps of:

For claims 8-12:

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prior to forming the insulating layer:

forming an oxide layer (112, fig, 2D) on the inner wall and bottom of the trench; forming an oxidation barrier layer (114, fig. 2D) on the oxide layer; and further comprising forming a capping layer (115, fig. 2D) between the oxidation barrier layer and the insulating layer (col. 4, Ins. 29-52).

Therefore it would have been obvious to those of ordinary skill in the art to combine Park with Laparra, because the layers disclosed by Park are protection layers for the trench.

4. Laparra and Park disclose all the steps of claims 1, 2 and 4-12 except for the material layer being formed being formed at a temperature of 700°C - 800°C and forming a etch-stop layer comprising polysilicon and a HTO layer which are sequentially stacked. However, Shin, column 5, lines 16-18, discloses that an LPCVD method comprises forming HTO and TEOS films at high temperatures in the range claimed by applicant. Therefore, Shin provides a specific temperature for different LPCVD layer, HTO and TEOS films, whereas Laparra just discloses the general conditions that the layer 40b is formed by a LPCVD method, which includes, but not limited to, TEOS. Park even says, column 3, lines 14-15, state that, "A high temperature oxide layer such as HTO and LP-TEOS oxide layers...", HTO and LP-TEOS layers form high temperature oxides. Therefore, from these two references HTO and LP-TEOS are considered as art equivalent layers. Also, that it would have been obvious to one having ordinary skill in the art at the time the invention was made to form an etch-stop layer, comprising polysilicon and a HTO layer which are sequentially stacked, since it

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has been held to be within the general skill of a worker in the art to select a known

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material on the basis of its suitability for the intended use as a matter of obvious design

choice. In re Leshin, 125 USPQ 416.

Specification

5. The disclosure is objected to because of the following informalities: Applicant

claims, in claim 10, an oxidation barrier layer comprising silicon oxide. However the

specification does not state what the oxidation barrier layer is comprised of.

Appropriate correction is required.

Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Ron E Pompey whose telephone number is (703) 305-

3016.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, John Niebling can be reached on (703) 308-3325. The fax phone numbers

for the organization where this application or proceeding is assigned are (703) 305-3432

for regular communications and (703) 305-3432 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or

proceeding should be directed to the receptionist whose telephone number is (703) 308-

0956.

Ron Pompey

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March 23, 2003

John F. Niebling

Supervisory Patent Examiner

Technology Center 2800